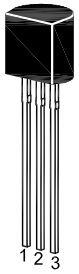
2SC2240

NPN Silicon Epitaxial Planar Transistor

The transistor is subdivided into two groups, G and L according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

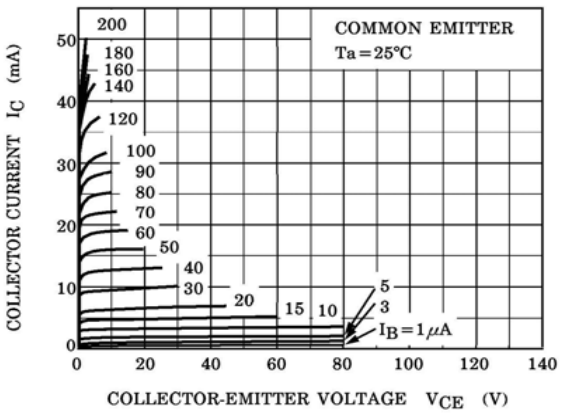
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	120	V
Collector Emitter Voltage	V_{CEO}	120	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

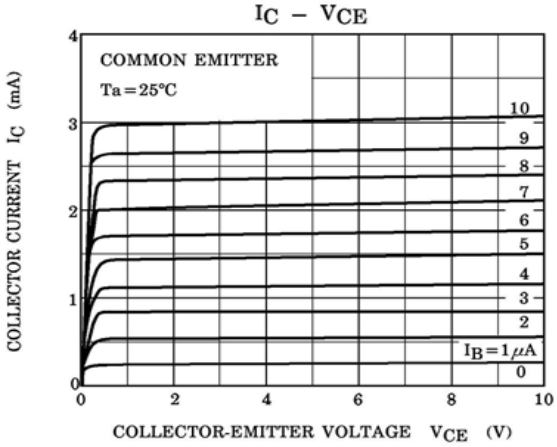
Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 6 V, I_C = 2 mA	Current Gain Group	G	h_{FE}	200	-	400	-
		L	h_{FE}	350	-	700	-
Collector Base Cutoff Current at V_{CB} = 120 V			I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at V_{EB} = 5 V			I_{EBO}	-	-	100	nA
Collector Emitter Breakdown Voltage at I_C = 1 mA			$V_{(BR)CEO}$	120	-	-	V
Collector Emitter Saturation Voltage at I_C = 10 mA, I_B = 1 mA			$V_{CE(sat)}$	-	-	0.3	V
Transition Frequency at V_{CE} = 6 V, I_C = 1 mA			f_T	-	100	-	MHz
Output Capacitance at V_{CB} = 10 V, f = 1 MHz			C_{ob}	-	-	6	pF

h_{FE} Classifications Symbol	GR
h_{FE} Range	200~400

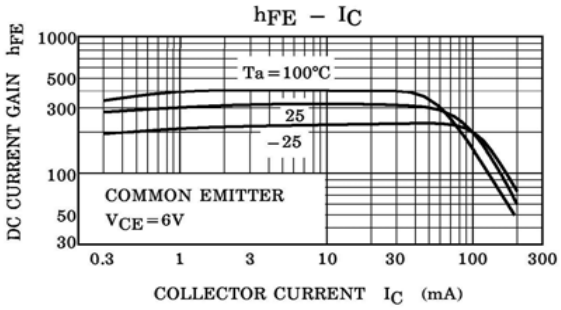
I_C – V_{CE}



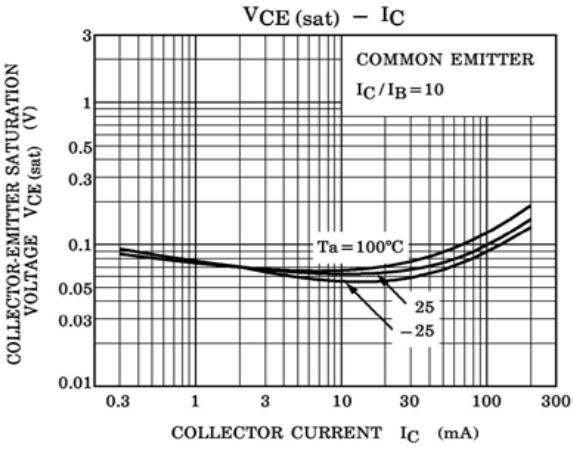
I_C – V_{CE}



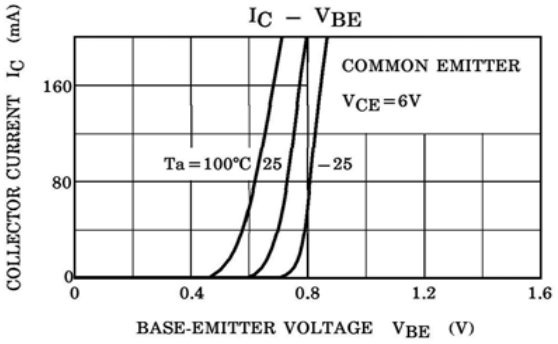
h_{FE} – I_C



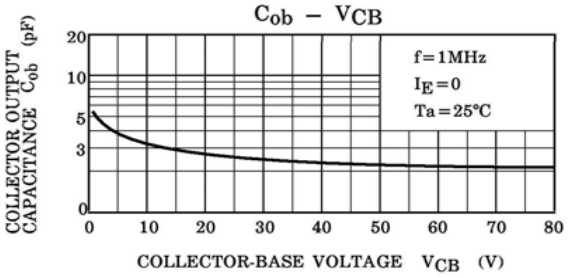
$V_{CE\,(sat)}$ – I_C



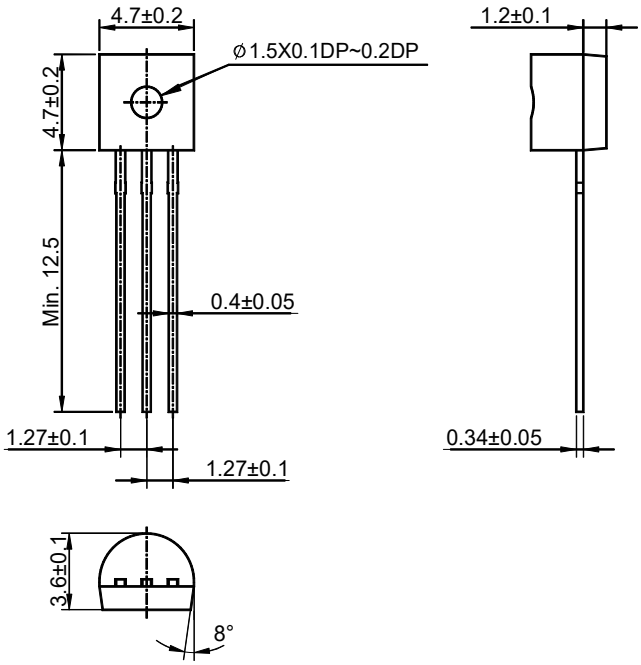
I_C – V_{BE}



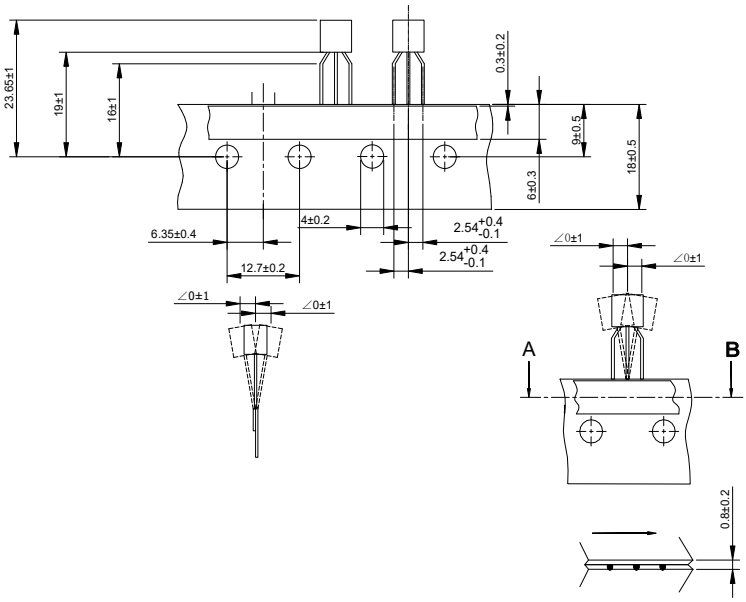
C_{ob} – V_{CB}



TO-92 Package Outline (Dimensions in millimeters)



TO-92 Ammo-Pack Outline (Dimensions in millimeters)



SECTION A–B

Packing information

Package	Bulk Packing			Ammo-Packing	
	Per Bag Qty	Per Box Qty	Per Carton Qty	Per Box Qty	Per Carton Qty
TO-92	1,000	5,000	50,000	4,000	20,000